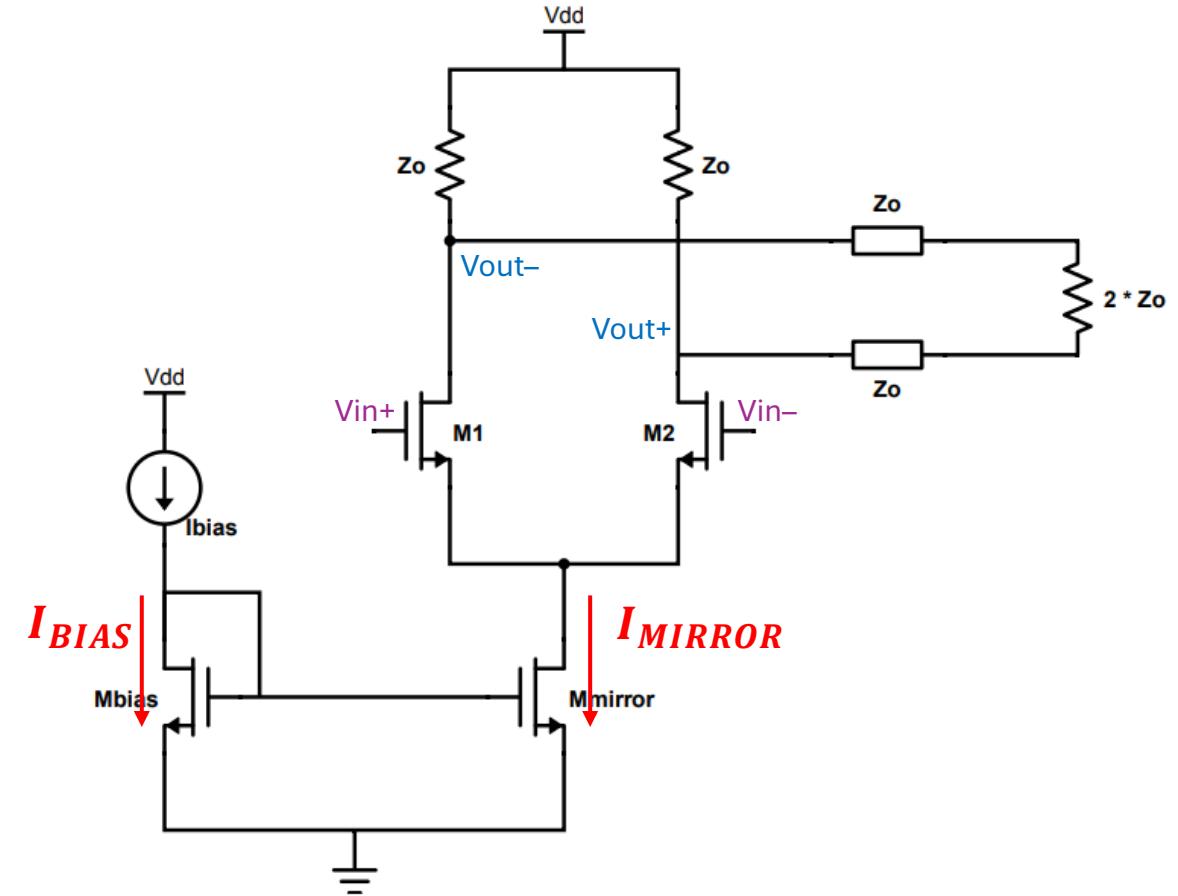


Tx Driver - CML

Notes on devices' initial sizing

Notes

- Start with DC Analysis.
 - Set $V_{IN+} = V_{dd}$ & $V_{IN-} = GND$.
 - Ensure that $I_{MIRROR} = I_{BIAS}$.



$$Z_o = 50 \Omega$$
$$V_{Swing(pk2pk)} = 500 mV$$
$$I_{BIAS} = \frac{500 mV}{50 \Omega} = 10 mA$$

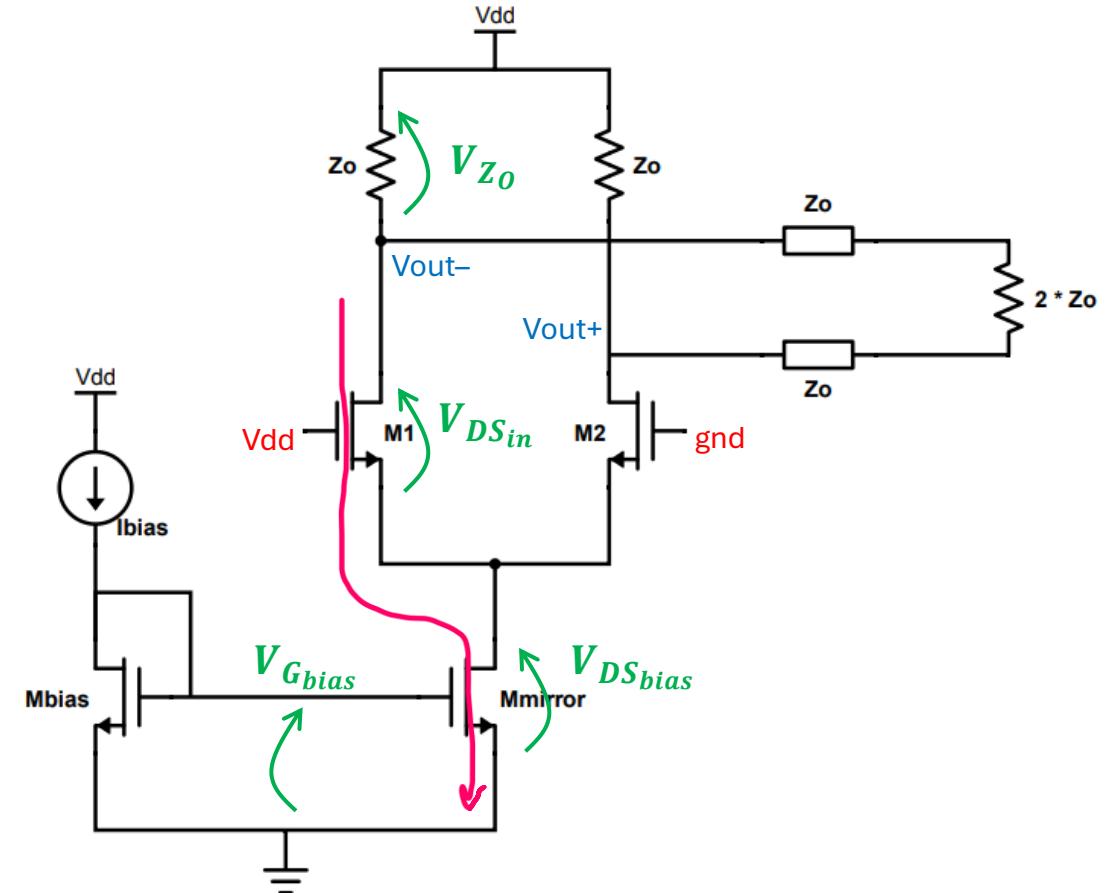
Notes

- Start with DC Analysis.
 - a) Set $V_{IN+} = V_{dd}$ & $V_{IN-} = GND$.
 - b) Ensure that $I_{MIRROR} = I_{BIAS}$.
 - c) Ensure there's no headroom issue.

We want M_{mirror} to be in SAT:

- $V_{DSbias(MIN)} = V_{Gbias} - V_{th}$
- $V_{DSbias} = V_{DD} - (I_{BIAS} * Z_O) - V_{DSin}$

❖
$$V_{DSin} < V_{DD} - (I_{BIAS} * Z_O) - V_{DSbias(MIN)}$$



Notes

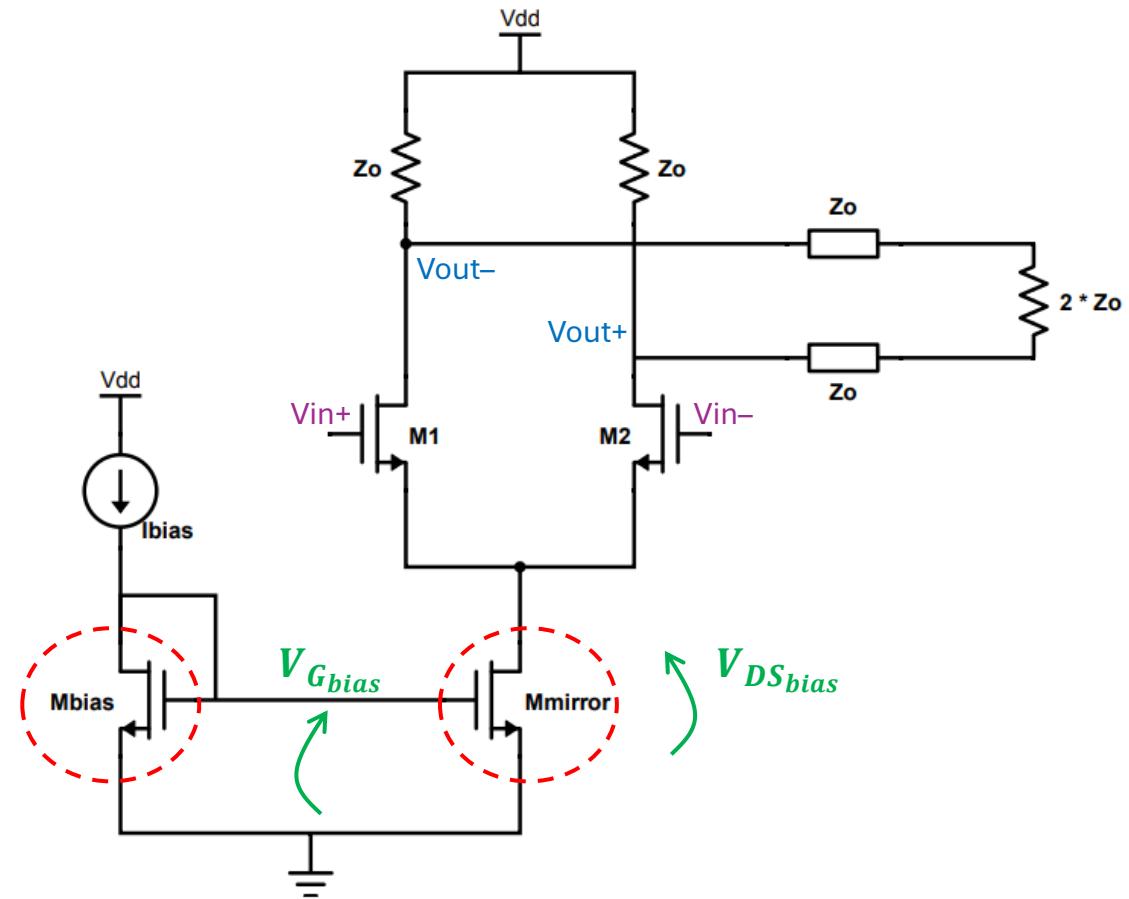
1. Current Mirror Devices:

→ Must be in Saturation

- a) Set $L > L_{\text{MIN}}$,
to reduce channel-length modulation effect.

 - b) Increase W to reduce $V_{G_{\text{bias}}}$,
making mirror device closer to SAT.

$$V_{DSbias} > V_{Gbias} - V_{th}$$

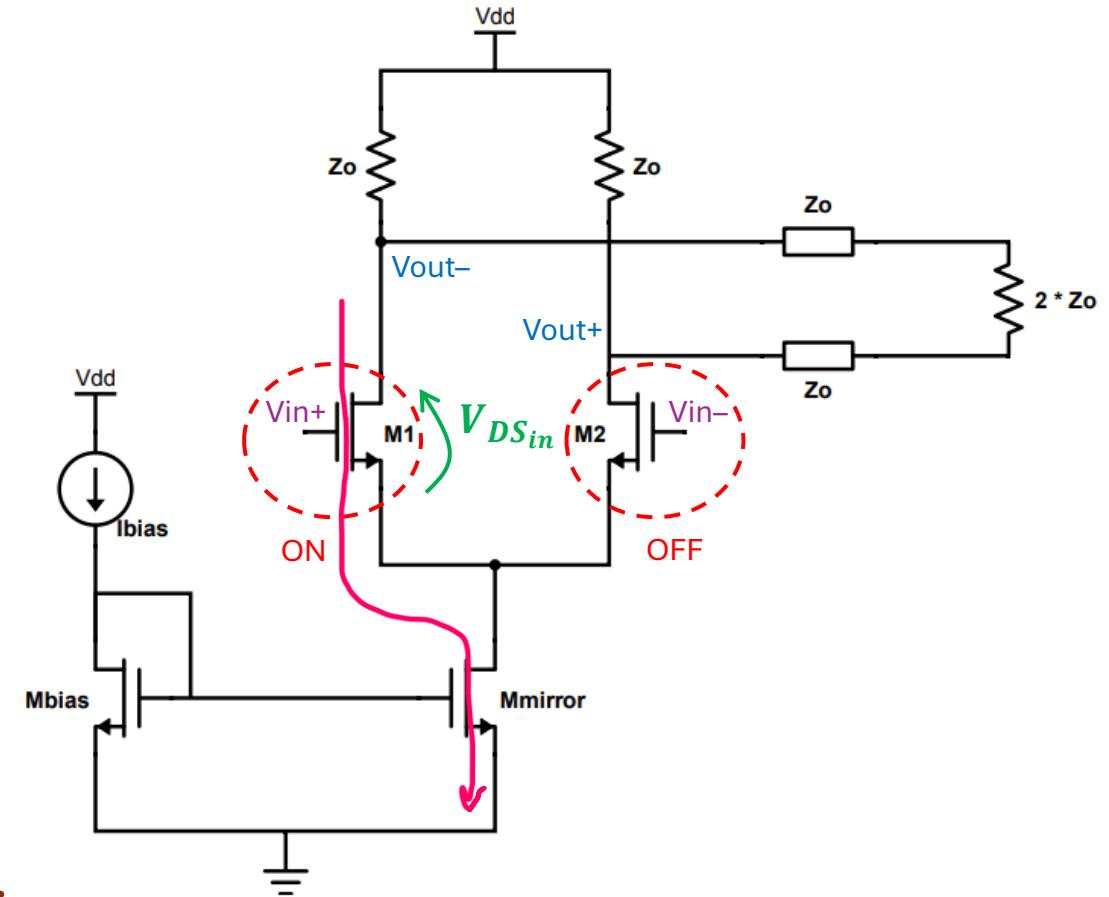


Notes

2. Input Devices:

→ Will either be in Triode (ON) or OFF

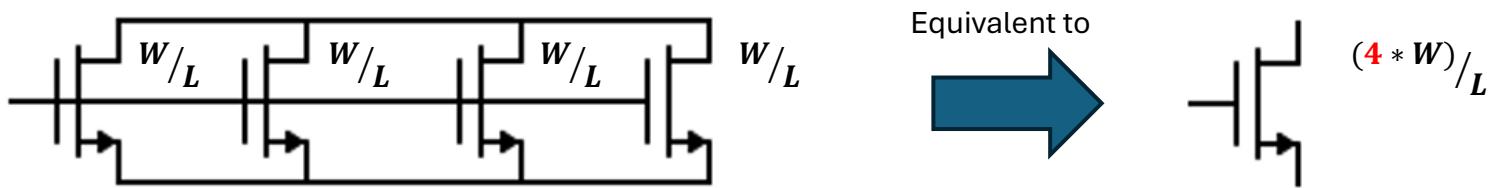
- a) Set $L = L_{MIN}$,
because these devices act as switches.
- b) Increase W to reduce $V_{DS_{in}}$,
by reducing the R_{ON} of the input devices.



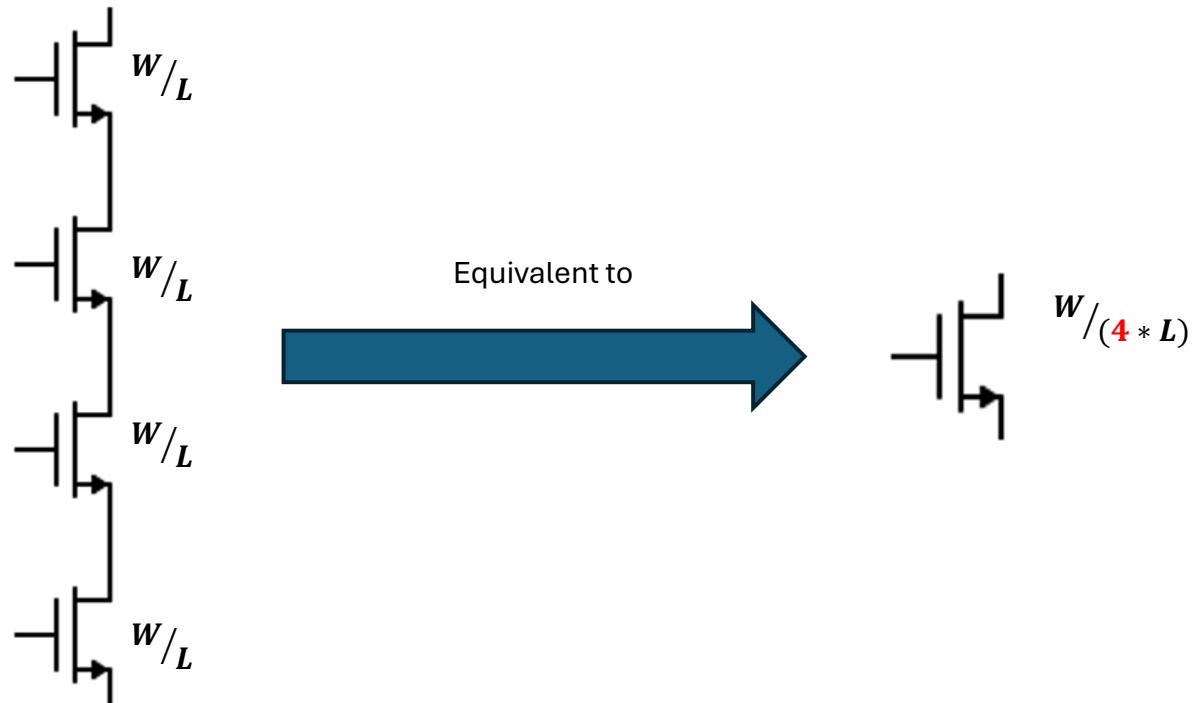
Notes

- We can increase the W or the L of a device by stacking them in either parallel or series.

➤ Parallel (increasing W):

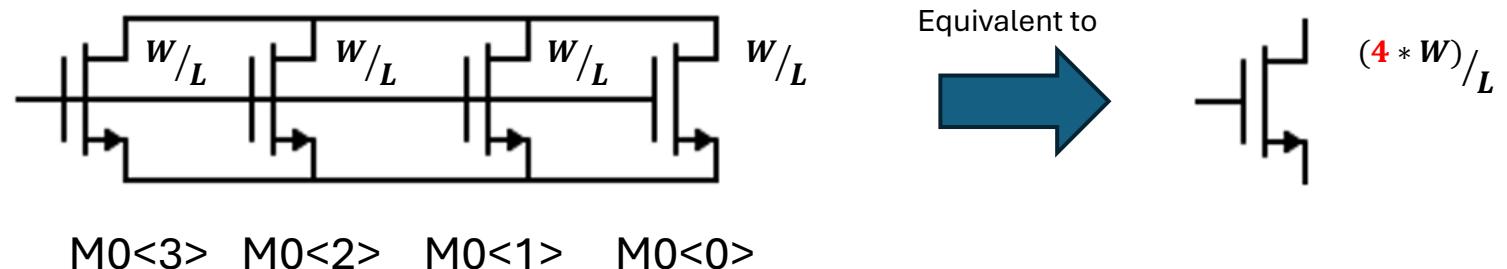


➤ Series (increasing L):



Notes

- How to implement 4 instances of a transistor in parallel ?



$M0<3:0>$

